

PRODUCT DATA SHEET



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Datasheet

s Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

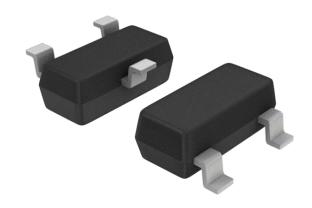


SZMMBZ5V6ALT1G

ESD Protection Diode Array

Features

- 350 Watts peak pulse power (tp = $8/20\mu$ s)
- Unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 \pm 30kV contact \pm 30kV air
- IEC 61000-4-4 (EFT) 40A(5/50ns)
- IEC 61000-4-5 (Lightning) 20A(8/20μs)



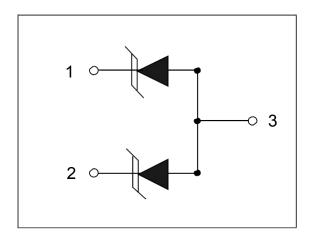
Applications

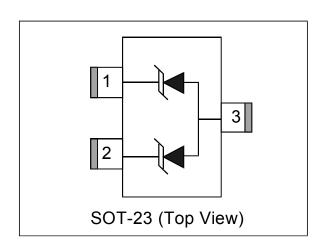
- Dataline
- Automatic Teller Machines
- Net works
- Power line

echanical Data

- SOT-23 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Schematic & PIN Configuration







Absolute Maximum Rating

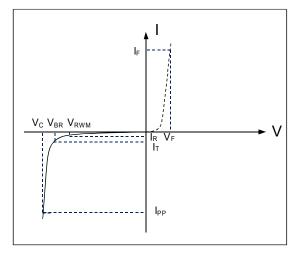
Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20μs)	P _{PP}	350	Watts
Peak Pulse Current (t _p =8/20μs) (note1)	I_{pp}	20	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	30 30	kV
Lead Soldering Temperature	T_{L}	260(10seconds)	$^{\circ}$
Junction Temperature	TJ	-55 to +125	$^{\circ}$
Storage Temperature	T_{stg}	-55 to +125	$^{\circ}$

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-OffVoltage	V_{RWM}				3.3	V
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	4.0	6.5	8.0	V
Reverse Leakage Current	I_R	V _{RWM} =3V,T=25°C		0.1	0.5	μΑ
Peak Pulse Current	I_{PP}	tp =8/20μs			20	A
Clamping Voltage	V _C	I _{PP} =20A,t _p =8/20μs			16	V
Junction Capacitance	C _j	$V_R = 0V$, $f = 1MHz$ (pin 1 \cdot pin 2 to pin 3)		200		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
Ірр	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
Ir	Maximum Reverse Leakage Current @ Vrwм
V _{BR}	Breakdown Voltage @ IT
Iт	Test Current





Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

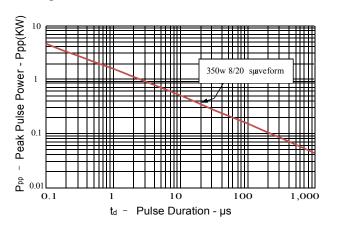


Figure 2: Power Derating Curve

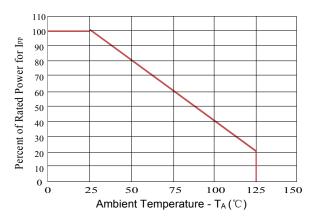


Figure3: Pulse Waveform

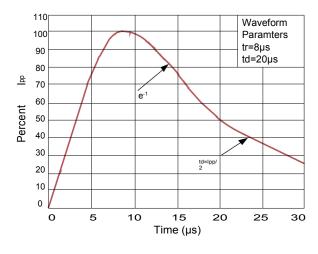
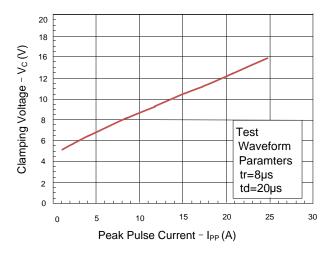


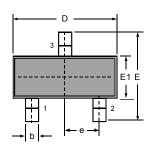
Figure 4: Clamping Voltage vs.lpp

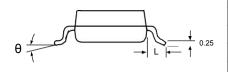






Outline Drawing - SOT-23







DIMENSIONS

SYMBOL MILLIMETER INCHES MIN MAX MIN MA A 0.900 1.150 0.035 0.04 A1 0.000 0.100 0.000 0.00	
A 0.900 1.150 0.035 0.04	
	15
A1 0.000 0.100 0.000 0.00	
)4
A2 0.900 1.050 0.035 0.04	¥1
D 2.800 3.000 0.110 0.11	18
b 0.300 0.500 0.012 0.02	20
E 2.250 2.550 0.089 0.10)0
E1 1.200 1.400 0.047 0.05	55
e 0.950 BSC 0.037 BSC	
L 0.300 0.500 0.012 0.02	20
θ 0 80 0 80)

SZMMBZ5V6ALT1G



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